RENESAS BCR08AS-12A

Triac

Low Power Use

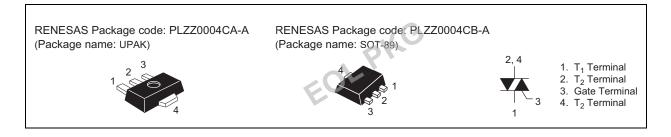
REJ03G0292-0400 Rev.4.00 Dec 10, 2008

Features

- $I_{T (RMS)} : 0.8 A$
- V_{DRM} : 600 V
- I_{FGTI}, I_{RGTI}, I_{RGT III}: 5 mA
- I_{FGT} : 10 mA

Outline

- Non-Insulated Type
- Planar Passivation Type
- Completed Pb Free



Applications

Hybrid IC, solid state relay, electric fan, washing machine, and other general purpose control applications

Maximum Ratings

Parameter	Symbol	Voltage class	Unit	
Falanetei	Symbol	12 (Mark BF)		
Repetitive peak off-state voltage ^{Note1}	V _{DRM}	600	V	
Non-repetitive peak off-state voltage ^{Note1}	V _{DSM}	720	V	

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	0.8	A	Commercial frequency, sine full wave 360° conduction, Ta = $40^{\circ}C^{Note3}$
Surge on-state current	I _{TSM}	8	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusing	l ² t	0.26	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P _{GM}	1	W	
Average gate power dissipation	P _{G (AV)}	0.1	W	
Peak gate voltage	V _{GM}	10	V	
Peak gate current	I _{GM}	1	Α	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	- 40 to +125	°C	
Mass	—	50	mg	Typical value

Notes: 1. Gate open.

REJ03G0292-0400 Rev.4.00 Dec 10, 2008 Page 1 of 7

Electrical Characteristics

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I _{DRM}	—	—	2.0	mA	Tj = 125°C, V _{DRM} applied
On-state voltage		V _{TM}	_	_	2.0	V	$Tc = 25^{\circ}C$, $I_{TM} = 1.2 A$, Instantaneous measurement
Gate trigger voltage ^{Note2}	Ι	V _{FGTI}	—	—	2.0	V	$\label{eq:constraint} \begin{array}{l} Tj = 25^\circC, \ V_D = 6 \ V, \ R_L = 6 \ \Omega, \\ R_G = 330 \ \Omega \end{array}$
	II	V_{RGTI}	_	_	2.0	V	
	III	V _{RGTIII}	_	_	2.0	V	
	IV	V _{FGTIII}	_	_	2.0	V	
Gate trigger current ^{Note2}	Ι	I _{FGTI}	_	_	5	mA	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	I _{RGTI}	_	_	5	mA	$R_G = 330 \Omega$
	III	I _{RGTIII}	_	_	5	mA	
	IV	I _{FGTIII}			10	mA	
Gate non-trigger voltage		V_{GD}	0.1	_	—	V	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-a)}	_	_	65	°C/W	Junction to ambient ^{Note3}
Critical-rate of rise of off-staticommutating voltage ^{Note4}	te	(dv/dt)c	0.5	—	—	V/µs	Tj = 125°C

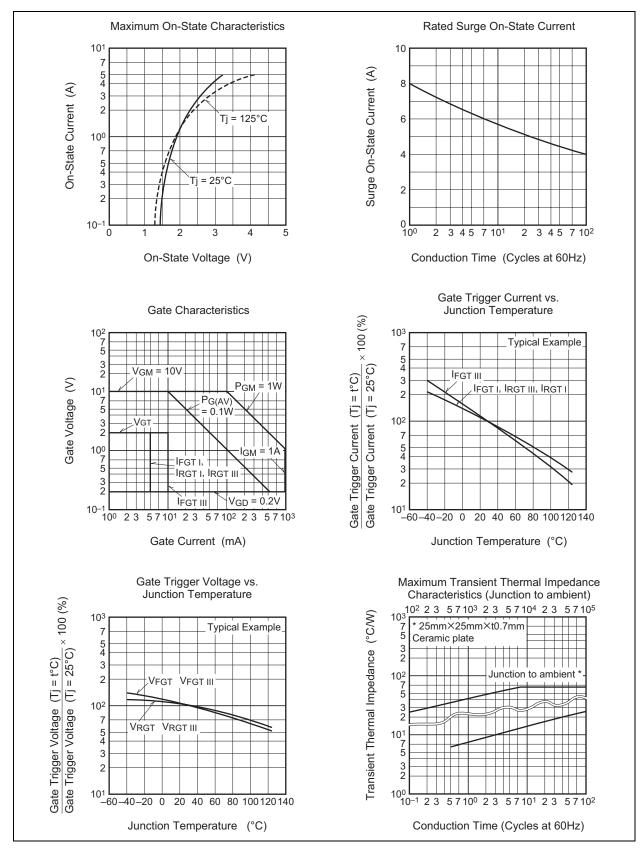
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. Soldering with ceramic plate (25 mm \times 25 mm \times t0.7 mm).

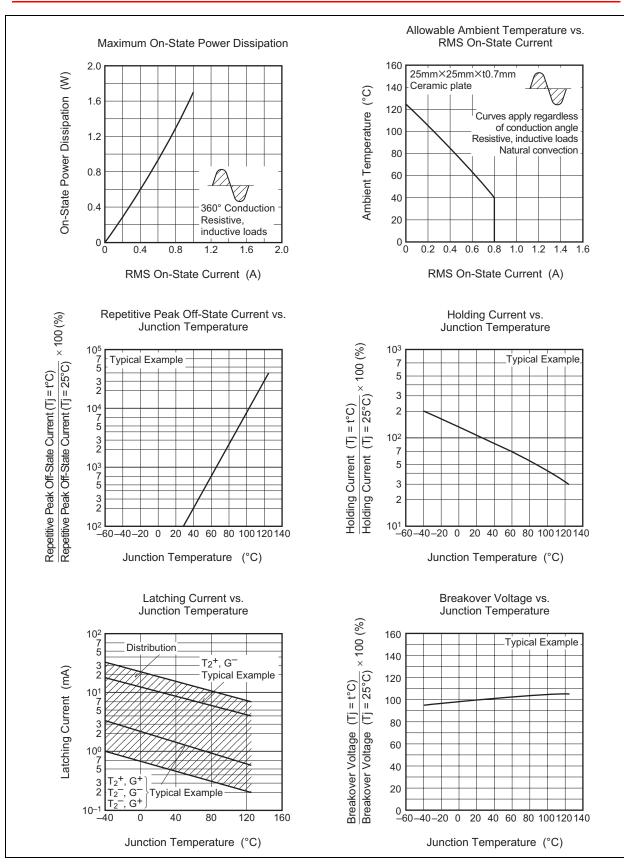
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature Tj = 125°C	Supply Voltage → Time		
 Rate of decay of on-state commutating current (di/dt)c = - 0.4 A/ms 	Main Current → Time		
3. Peak off-state voltage V _D = 400 V	Main Voltage → Time (dv/dt)c V _D		

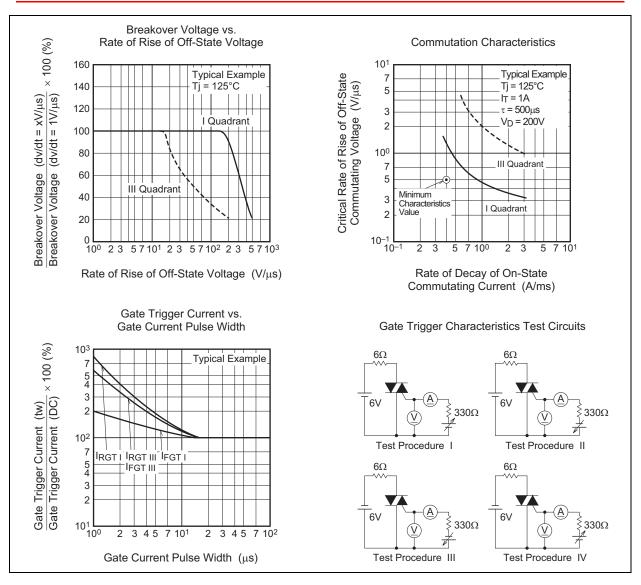
Performance Curves



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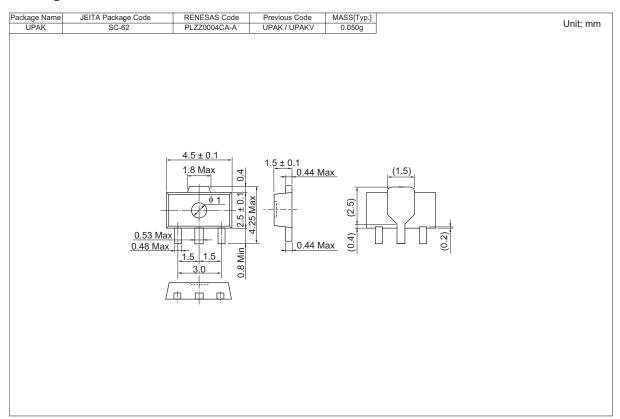


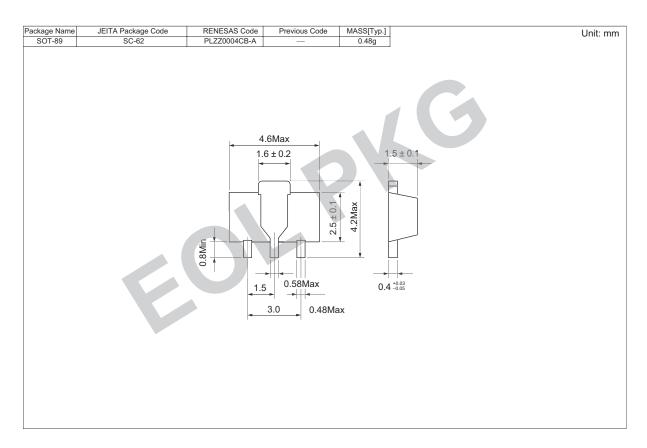
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Downloaded from Elcodis.com electronic components distributor

Package Dimensions





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Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	4000	Type name –T +Direction (1 or 2)+4	BCR08AS-12A-T14

Note : Please confirm the specification about the shipping in detail.

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http://www.renesas.com

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